

Publication List of Chenhsin Lien (2008-2012)

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1. C. C. Hung, W. S. Liao, S. Y. Huang, K. M. Chen, G. W. Huang, C. H. Lien, "Effect of mixed-mode electrical stress on high-frequency and RF power characteristics of SiGe hetero-junction bipolar transistors", *Jpn. J. Appl. Phys.*, vol. 47, no. 4, pp. 2872-2876, Apr. 2008.
2. Heng-Yuan Lee, Pang-Shiu Chen, Tai-Yuan Wu, Ching-Chiun Wang, Pei-Jer Tzeng, Cha-Hsin Lin, Frederick Chen, Ming-Jinn Tsai, Chenhsin Lien, "Electrical evidence of unstable anodic interface in Ru/HfO_x/TiN unipolar resistive memory", *Appl. Phys. Lett.*, vol. 92, no.14, Apr. 2008. **(Impact Factor 前 15%)**
3. Der-Sheng Chao, Chenhsin Lien, Yan-Kai Chen, Yi-Bo Liao, Meng-Hsueh Chiang, Ming-Jer Kao, Ming-Jinn Tsai, "A comprehensive parameterized model of phase-change memory cell for HSPICE circuit simulation", *Jpn. J. Appl. Phys.*, vol. 47, no. 4, pp. 2696-2700, Apr. 2008.
4. Der-Sheng Chao, Chenhsin Lien, Chain-Ming Lee, Yin-Chan Chen, Jyi-Tyan Yeh, Fred Chen, Ming-Jung Chen, Philip H. Yen, Ming-Jer Kao, Ming-Jinn Tsai, "Impact of incomplete set programming on the performance of phase change memory cell", *Appl. Phys. Lett.*, vol. 92, no.6, Apr. 2008. **(Impact Factor 前 15%)**
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8. San-Pin Yeh, Chun-Hsing Shih, Jeng Gong, and Chenhsin Lien, "Latent noise in Schottky barrier MOSFETs," *Journal of Statistical Mechanics: Theory and Experiment*, P01036 (focus issue), Jan. 2009. **(Impact Factor 前 15%)**
9. Y. L. Tai, J. W. Lee, C. H. Lien, "Investigation Semiconductor Investigation of Minority Carrier Distribution in Semiconductor-Controlled Rectifier Devices and

- the Impact on Electrostatic Discharge Applications” *Jpn. J. Appl. Phys.*, Vol. 48, Issue 2, Feb. 2009.
10. Ching-Yuan Ho, Chenhsin Lien, C. H. Liu, Y. M. Lin and S. Pittikoun, “Effect of Rapid Thermal Annealing in N₂ and Stacked Layer on SiO₂-Al₂O₃-SiO₂ Characteristics for Interpoly Silicon Dielectrics,” *Jpn. J. Appl. Phys.*, Vol. 48, pp. 046503, April 2009.
 11. Heng-Yuan Lee, Pang-Shiu Chen, Tai Yuan Wu, Frederick Chen, Ching-Chiun Wang, Pei-Jer Tzeng, Cha-Hsin Lin, Ming-Jinn Tsai and Chenhsin Lien, “HfO_x Bipolar Resistive Memory with Robust Endurance Using AlCu as Buffer Electrode”, *IEEE Electron Device Lett.*, vol. 30, no. 7, pp. 703-705, July 2009. **(Impact Factor 前 15%)**
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 16. Ya-Li Tai, Jam-Wem Lee, and Chen-Hsin Lien, “Local Oxidation Fin-Field-Effect -Transistor Structure for Nanodevice Applications,” *Jpn. J. Appl. Phys.*, vol. 49, pp. 044301, April 2010.
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22. Yu-Sheng Chen, Heng-Yuan Lee, Pang-Shiu Chen, Pei-Yi Gu, Wen-Hsing Liu, Wei-Su Chen, Yen-Ya Hsu, Chen-Han Tsai, Frederick Chen, Ming-Jinn Tsai, and Chenhsin Lien, "Good endurance and Memory Window for Ti/HfO_x Pillar RRAM at 50-nm Scale by Optimal Encapsulation Layer," *IEEE Electron Device Letters*, vol. 32, no. 3, pp. 1477-1479, March 2011. **(Impact Factor 前 15%)**
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26. Pei-Ren Jeng, KuanHua Chen, Gwo-Jen Hwang, Chen-Man Tien, Chenhsin Lien, Kiwing To, and Y. C. Chou, "Packaging of granular bead chain," *EPL*, vol. 96, No. 4, pp. 44005, Nov. 2011.
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4. Henry J. H. Chen, Ming-Tien Huang, Yu-Wu Wang, Sun Zen Chen, Puru Lin, Chenhsin Lien, Barry B. L. Yeh and Wei-Yang Chou, "Fabrication of Au/PEDOT/PSS Stacked Electrodes of OTFTs by Imprinting Technology," *216th ECS Meeting*, Vienna, Austria, 2009.
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13. Shyh-Shyuan Sheu, Meng-Fan Chang, Ku-Feng Lin, Che-Wei Wu, Yu-Sheng Chen, Pi-Feng Chiu, Chia-Chen Kuo, Yih-Shan Yang, Pei-Chia Chiang, Wen-Pin Lin, Che-He Lin, Heng-Yuan Lee, Pei-Yi Gu, Sum-Min Wang, Frederick T. Chen, Keng-Li Su, Chen-Hsin Lien, Kuo-Hsing Cheng, Hsin-Tun Wu, Tzu-Kun Ku, Ming-Jer Kao, and Ming-Jinn Tsai, “A 4Mb Embedded SLC Resistive-RAM Macro with 7.2ns Read-Write Random-Access Time and 160ns MLC-Access Capability,” , pp. 200-202, **2011 IEEE International Solid State Circuits Conference Digest Technical Papers**, 2011.
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